Application No.: 10/584,414 Docket No.: 0757-0316PUS1

Reply to Office Action dated April 2, 2009

AMENDMENTS TO THE CLAIMS

1. (Currently Amended) A microwave frequency converter comprising:

an RF amplifier eapable of changing awhose gain is adjustable to any value within a range

from an amplified state to an attenuated state;

and a control circuit for applyingthat applies a gain control voltage to the RF amplifier;

wherein the control circuit controls the gain control voltage to be applied to the RF amplifier

so as to eausesuch that the gain of the RF amplifier to beis in the attenuated state during a period

of time including a time during which a transmission section performs oscillation and times

therebefore and thereafter, and to be in the amplified state during any period of time other than

the cocioic and dictoater, and to be in the tanpaness state than 5 and 5

the period of time; and

further wherein the RF amplifier does not perform attenuation when its gain value is

associated with an amplified state.

2. (Previously Presented) The microwave frequency converter according to claim 1, wherein the

control circuit continuously changes the gain control voltage to continuously change the gain of

the RF amplifier from a predetermined gain value in the amplified state to a predetermined gain

value in the attenuated state, or from a predetermined gain value in the attenuated state to a

predetermined gain value in the amplified state.

3. (Previously Presented) The microwave frequency converter according to claim 1, wherein the

control circuit instantaneously changes the gain control voltage to instantaneously change the

gain of the RF amplifier from a predetermined gain value in the amplified state to a

predetermined gain value in the attenuated state, or from a predetermined gain value in the

attenuated state to a predetermined gain value in the amplified state.

4. (Currently Amended) The microwave frequency converter according to claim 3, wherein the

RF amplifier employs includes a FET device or a HEMT device which is operated by applying a

negative voltage to a gate thereof and a positive voltage to a drain thereof, and the control circuit

simultaneously switches ON/OFF a the gate voltage and a drain voltages to be applied to the gate

and the drain of the device to cause such that the gain of the RF amplifier to beis in the attenuated

state when the gate voltage and the drain voltage are switched ON, and to be in the amplified

state when the gate voltage and the drain voltage are switched OFF.

5. (New) A microwave frequency converter comprising:

an RF amplifier whose gain is adjustable to any value within a range from an amplified

state to an attenuated state;

and a control circuit that applies a gain control voltage to the RF amplifier;

wherein the control circuit controls the gain control voltage such that the gain of the RF

amplifier is in the attenuated state during a period of time including a time during which a

transmission section performs oscillation and times therebefore and thereafter, and to be in the

amplified state during any period of time other than the period of time; and

further wherein both the amplification and attenuation aspects of the amplifier gain are

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directly controlled by the gain control voltage.

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6. (New) The microwave frequency converter according to claim 5, wherein the RF amplifier is a FET.